

# DATA SHEET



## NPN SILICON RF TRANSISTOR NE462M02 / 2SC5338 JEITA Part No.

### NPN SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW DISTORTION AMPLIFIER 4-PIN POWER MINIMOLD

#### FEATURES

- High gain:  $|S_{21e}|^2 = 10$  dB TYP. @  $V_{CE} = 5$  V,  $I_c = 50$  mA,  $f = 1$  GHz
- Low distortion, low voltage:  $IM_2 = -55$  dB TYP.,  $IM_3 = -76$  dB TYP. @  $V_{CE} = 5$  V,  $I_c = 50$  mA,  $V_{in} = 105$  dB $\mu$ V/75 $\Omega$
- 4-pin power minimold package with improved gain from the NE46234 / 2SC4703

#### ★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE462M02-AZ 2SC5338-AZ	25 pcs (Non reel)	• Magazine case
NE462M02-T1-AZ 2SC5338-T1-AZ	1 kpcs/reel	• 12 mm wide embossed taping • Collector face the perforation side of the tape

**Remark** To order evaluation samples, please contact your nearby sales office.  
Unit sample quantity is 25 pcs.

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V <sub>CB0</sub>	25	V
Collector to Emitter Voltage	V <sub>CE0</sub>	12	V
Emitter to Base Voltage	V <sub>EB0</sub>	2.5	V
Collector Current	I <sub>c</sub>	150	mA
Total Power Dissipation	P <sub>tot</sub> <small>Note</small>	1.8	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C

**Note** Mounted on 16 cm<sup>2</sup> × 0.7 mm (t) ceramic substrate (Copper plating)

**Because this product uses high-frequency technology, avoid excessive static electricity, etc.**

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**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit	
<b>DC Characteristics</b>							
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0 mA	–	–	1.5	μA	
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>BE</sub> = 2 V, I <sub>C</sub> = 0 mA	–	–	1.5	μA	
DC Current Gain	h <sub>FE</sub> <sup>Note 1</sup>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA	50	–	250	–	
<b>RF Characteristics</b>							
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA	–	6.0	–	GHz	
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA, f = 1 GHz	8.5	10	–	dB	
Noise Figure	NF	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA, f = 1 GHz	–	–	3.5	dB	
Reverse Transfer Capacitance	C <sub>re</sub> <sup>Note 2</sup>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0 mA, f = 1 MHz	–	1.0	2.0	pF	
2nd Order Intermodulation Distortion	IM <sub>2</sub>	I <sub>C</sub> = 50 mA, V <sub>in</sub> = 105 dBμV/75 Ω, f = 190 – 90 MHz	V <sub>CE</sub> = 5 V	–	–55	–	dB
			V <sub>CE</sub> = 10 V	–	–63	–	
3rd Order Intermodulation Distortion	IM <sub>3</sub>	I <sub>C</sub> = 50 mA, V <sub>in</sub> = 105 dBμV/75 Ω, f = 2 × 190 – 200 MHz	V <sub>CE</sub> = 5 V	–	–76	–	dB
			V <sub>CE</sub> = 10 V	–	–83	–	

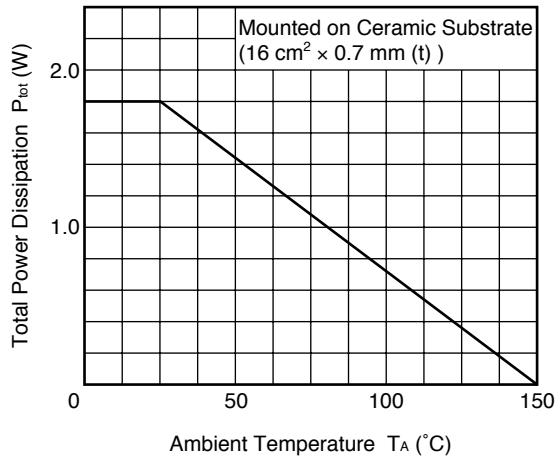
- Notes 1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%  
**2.** Collector to base capacitance when the emitter grounded

**h<sub>FE</sub> CLASSIFICATION**

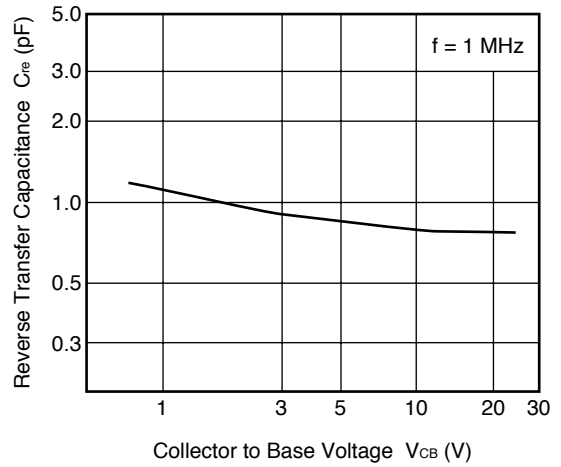
Rank	SH	SF	SE
Marking	SH	SF	SE
h <sub>FE</sub> Value	50 to 100	80 to 160	125 to 250

★ TYPICAL CHARACTERISTICS (Unless otherwise specified,  $T_A = +25^\circ\text{C}$ )

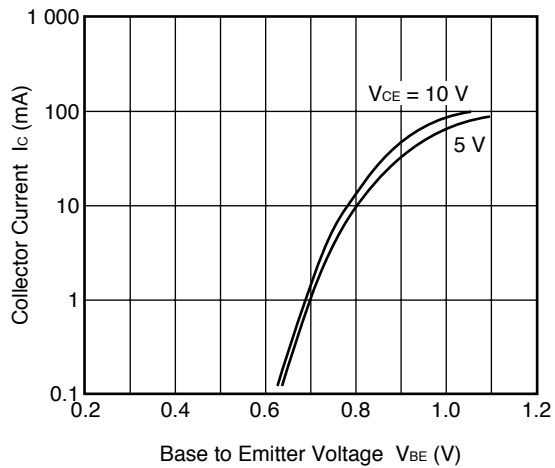
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



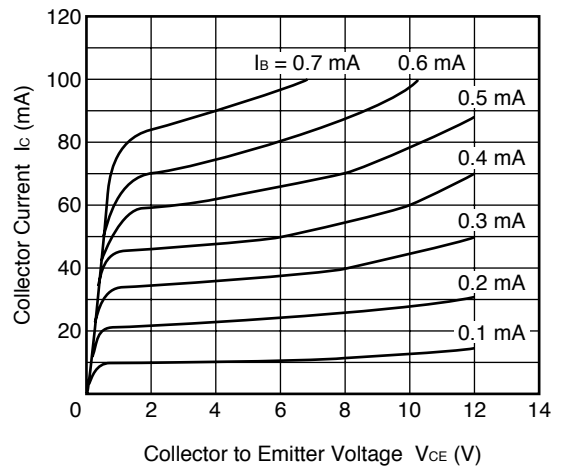
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



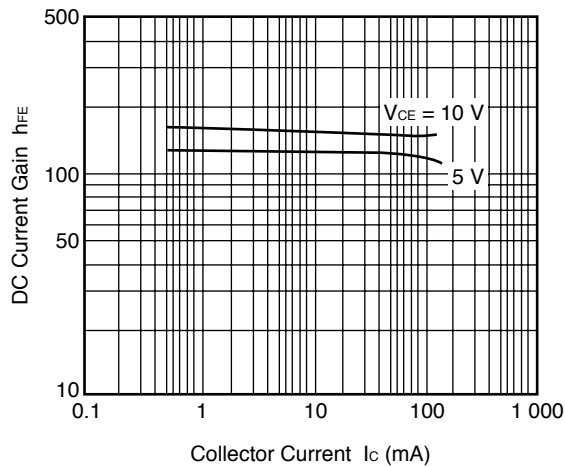
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



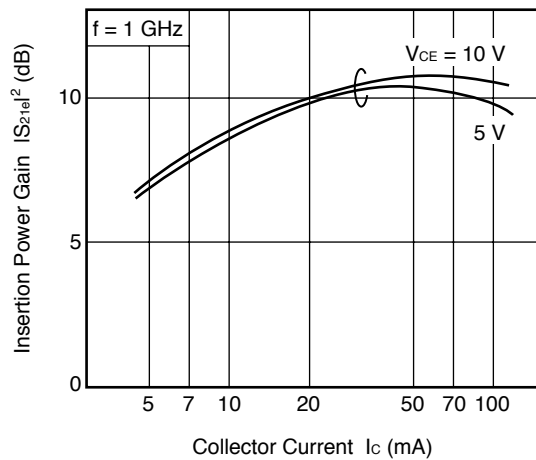
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



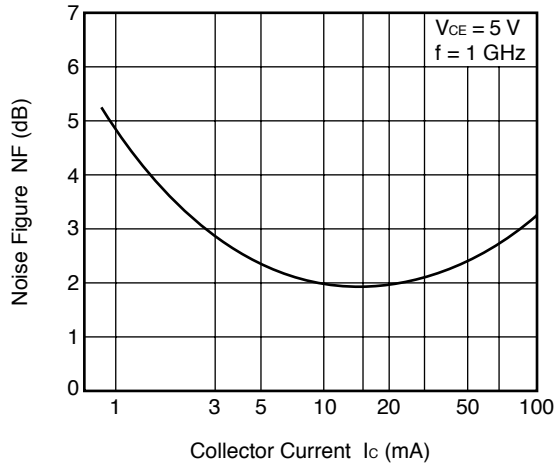
DC CURRENT GAIN vs. COLLECTOR CURRENT



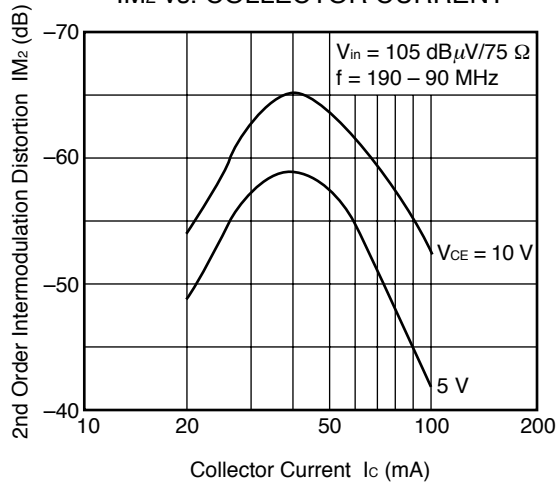
INSERTION POWER GAIN vs. COLLECTOR CURRENT



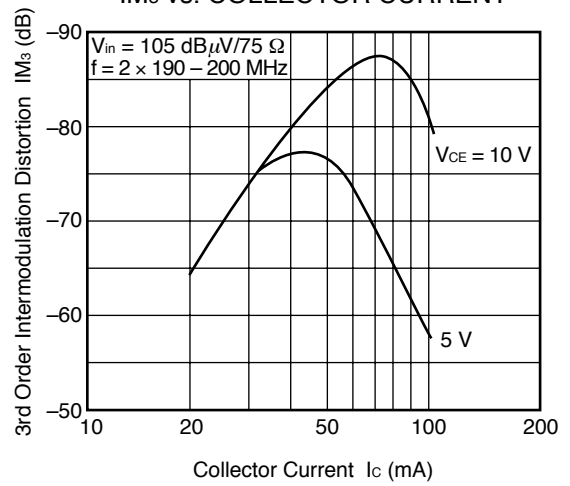
NOISE FIGURE vs. COLLECTOR CURRENT



IM<sub>2</sub> vs. COLLECTOR CURRENT



IM<sub>3</sub> vs. COLLECTOR CURRENT



**Remark** The graphs indicate nominal characteristics.

**S-PARAMETERS**

V<sub>CE</sub> = 5 V, I<sub>C</sub> = 50 mA

Frequency (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)
0.1	0.642	-61.5	19.689	138.5	0.026	64.9	0.603	-39.7
0.2	0.521	-103.0	13.393	116.8	0.045	53.1	0.461	-62.1
0.3	0.464	-123.8	9.708	106.3	0.053	57.8	0.359	-72.8
0.4	0.428	-137.2	7.480	99.5	0.059	62.1	0.304	-75.7
0.5	0.408	-147.7	6.078	94.5	0.072	63.7	0.289	-79.4
0.6	0.390	-154.3	5.104	91.3	0.080	65.9	0.275	-83.2
0.7	0.374	-161.1	4.394	88.6	0.088	66.2	0.277	-82.8
0.8	0.360	-163.9	3.880	86.2	0.097	68.9	0.261	-85.0
0.9	0.348	-168.0	3.527	84.5	0.110	72.1	0.271	-81.6
1.0	0.351	-175.1	3.224	83.3	0.119	72.0	0.268	-79.9
1.1	0.329	-179.9	3.111	81.8	0.125	76.4	0.276	-75.5
1.2	0.328	179.8	3.078	78.9	0.144	73.7	0.321	-75.3
1.3	0.319	171.9	2.914	69.6	0.157	77.8	0.320	-82.4
1.4	0.297	168.9	2.501	66.2	0.166	75.7	0.291	-83.6
1.5	0.307	165.2	2.285	65.3	0.182	77.7	0.325	-83.4
1.6	0.308	159.6	2.115	63.9	0.192	77.7	0.305	-82.7
1.7	0.303	156.6	1.993	62.9	0.201	77.4	0.313	-81.7
1.8	0.309	154.1	1.880	62.0	0.219	75.5	0.327	-83.5
1.9	0.312	150.3	1.786	60.8	0.222	74.9	0.321	-86.3
2.0	0.315	148.4	1.704	59.9	0.242	75.9	0.341	-91.2

V<sub>CE</sub> = 5 V, I<sub>C</sub> = 100 mA

Frequency (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)
0.1	0.647	-73.2	21.091	134.7	0.039	58.3	0.793	-45.3
0.2	0.529	-112.8	13.280	113.6	0.060	53.9	0.561	-71.0
0.3	0.480	-133.5	9.390	103.3	0.072	54.2	0.409	-82.3
0.4	0.459	-146.3	7.213	96.7	0.079	55.6	0.360	-86.1
0.5	0.443	-155.4	5.826	92.0	0.090	58.6	0.333	-90.2
0.6	0.424	-160.9	4.890	89.2	0.102	57.6	0.315	-95.6
0.7	0.406	-166.8	4.206	86.9	0.111	61.4	0.297	-96.0
0.8	0.401	-169.8	3.711	84.3	0.120	64.2	0.292	-95.6
0.9	0.396	-173.9	3.372	82.7	0.135	66.9	0.288	-93.9
1.0	0.391	-178.9	3.093	81.8	0.143	67.0	0.294	-91.3
1.1	0.361	176.3	2.950	80.4	0.157	67.4	0.298	-86.5
1.2	0.366	175.3	2.984	77.2	0.166	67.9	0.338	-86.4
1.3	0.363	167.7	2.788	67.5	0.178	68.5	0.359	-94.6
1.4	0.337	165.3	2.413	64.6	0.192	71.3	0.320	-95.5
1.5	0.352	160.9	2.194	63.4	0.210	70.8	0.322	-96.3
1.6	0.349	157.0	2.017	61.7	0.220	68.8	0.314	-92.3
1.7	0.352	154.7	1.900	60.9	0.236	69.4	0.329	-91.1
1.8	0.353	152.0	1.810	60.3	0.248	69.1	0.339	-93.7
1.9	0.354	147.9	1.730	58.8	0.252	68.8	0.336	-98.1
2.0	0.354	146.6	1.633	57.8	0.261	66.2	0.342	-98.2

V<sub>CE</sub> = 10 V, I<sub>C</sub> = 50 mA

Frequency (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)
0.1	0.699	-59.3	21.061	140.1	0.037	68.2	0.860	-37.6
0.2	0.540	-97.0	14.088	118.4	0.057	57.8	0.629	-62.0
0.3	0.461	-119.1	10.216	107.1	0.066	55.0	0.464	-72.1
0.4	0.423	-133.2	7.898	99.9	0.076	56.4	0.409	-77.1
0.5	0.403	-144.4	6.431	95.0	0.087	56.6	0.375	-80.6
0.6	0.383	-150.8	5.407	91.8	0.099	58.7	0.363	-86.2
0.7	0.355	-158.1	4.640	89.3	0.110	59.6	0.327	-87.7
0.8	0.338	-161.3	4.093	86.7	0.118	61.4	0.323	-87.8
0.9	0.333	-165.1	3.723	84.9	0.129	63.9	0.310	-86.0
1.0	0.322	-172.7	3.406	84.0	0.137	66.0	0.324	-83.2
1.1	0.303	-177.8	3.245	82.6	0.150	65.6	0.333	-79.9
1.2	0.306	-178.3	3.278	79.5	0.159	66.2	0.371	-80.5
1.3	0.295	171.3	3.074	69.9	0.168	67.6	0.377	-86.5
1.4	0.276	171.0	2.644	67.0	0.180	69.7	0.347	-86.7
1.5	0.283	164.5	2.397	66.2	0.198	70.5	0.363	-88.4
1.6	0.282	159.5	2.208	64.7	0.208	69.1	0.342	-85.6
1.7	0.283	157.3	2.088	64.1	0.220	70.0	0.344	-86.0
1.8	0.287	154.8	1.986	62.6	0.232	70.0	0.366	-87.8
1.9	0.290	150.4	1.886	61.7	0.247	69.4	0.371	-89.3
2.0	0.300	148.7	1.787	60.7	0.254	68.4	0.361	-92.9

V<sub>CE</sub> = 10 V, I<sub>C</sub> = 100 mA

Frequency (GHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)
0.1	0.651	-64.8	21.694	136.2	0.029	62.4	0.588	-43.4
0.2	0.520	-106.4	14.288	114.6	0.042	53.0	0.435	-62.7
0.3	0.460	-126.5	10.214	104.5	0.051	56.6	0.330	-73.0
0.4	0.420	-140.1	7.822	98.1	0.061	58.4	0.284	-77.1
0.5	0.395	-150.0	6.355	93.2	0.070	65.6	0.270	-78.8
0.6	0.384	-156.3	5.314	90.3	0.077	67.0	0.257	-82.2
0.7	0.367	-162.9	4.569	87.8	0.089	70.9	0.258	-82.1
0.8	0.350	-165.5	4.037	85.6	0.095	71.6	0.241	-82.9
0.9	0.343	-169.3	3.649	83.8	0.106	72.5	0.257	-79.5
1.0	0.339	-177.1	3.353	82.8	0.117	73.9	0.258	-79.3
1.1	0.316	177.9	3.193	81.0	0.125	75.0	0.261	-73.6
1.2	0.315	179.4	3.217	78.4	0.142	75.5	0.311	-72.3
1.3	0.309	170.1	3.026	69.1	0.152	78.1	0.324	-80.4
1.4	0.287	165.6	2.592	65.9	0.164	75.6	0.280	-81.0
1.5	0.303	161.9	2.374	65.2	0.173	80.5	0.308	-82.6
1.6	0.293	157.9	2.179	63.5	0.187	78.1	0.295	-81.4
1.7	0.301	153.7	2.054	62.4	0.200	78.2	0.307	-78.7
1.8	0.303	150.7	1.945	61.4	0.214	75.9	0.313	-82.1
1.9	0.306	148.8	1.840	60.5	0.225	75.4	0.321	-82.8
2.0	0.311	147.2	1.753	59.7	0.240	75.0	0.332	-86.9



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